

MURJ1220CT

Rev.E Mar.-2016

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Rectified Forward Current	I_F	2x6	A
Non Repetitive Peak Surge Current	I_{FSM}	100	A
Thermal Resistance Junction to Case	R_{JC}	2.9	/W
Storage Temperature Range	T_j T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=2.0A(T_C=25^\circ C)$		0.82		V
		$I_F=2.0A(T_C=125^\circ C)$		0.68		V
		$I_F=6.0A(T_C=25^\circ C)$		0.92	1.0	V
		$I_F=6.0A(T_C=125^\circ C)$		0.82	0.9	V
Instantaneous Reverse Current	I_R	$V_R=200V(T_a=25^\circ C)$			10	μA
		$V_R=200V(T_a=125^\circ C)$			150	μA
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_R=1.0A$ $I_{RR}=0.25A$			35	ns

/Notes

1. effect.

2. single chip

/Short duration pulse test used to minimize self-heating

/ Unless otherwise noted, values for the parameters of a

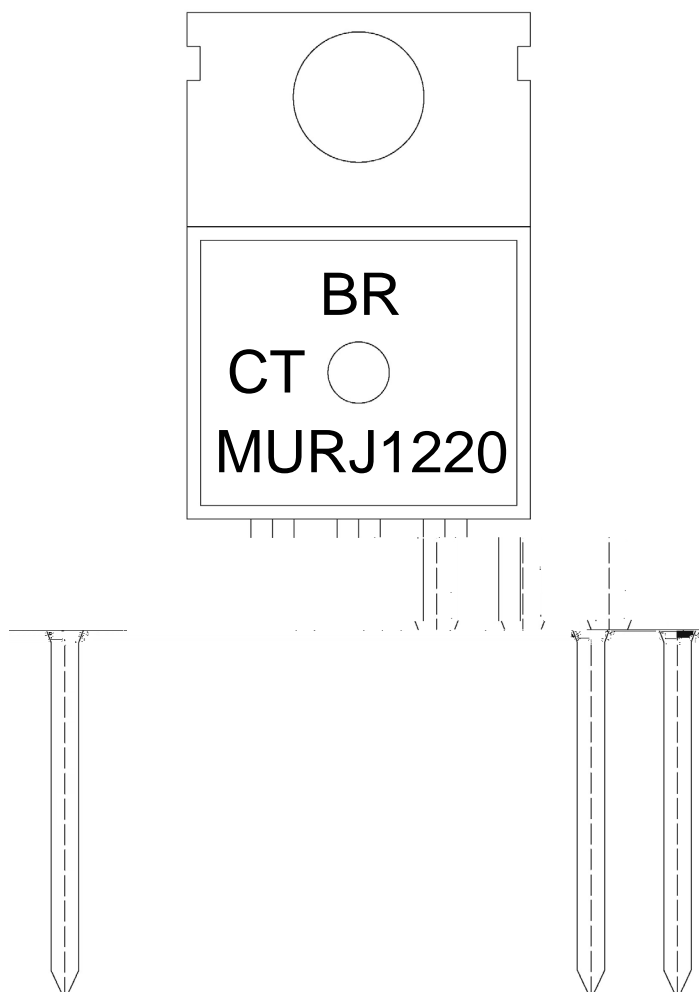
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蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

/ Marking Instructions



BR

MURJ1220

CT:

Note:

BR: Company Code

MURJ1220 Product Type.

CT: Internal Structure

****: Lot No. Code, code change with Lot No.

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DATA SHEET